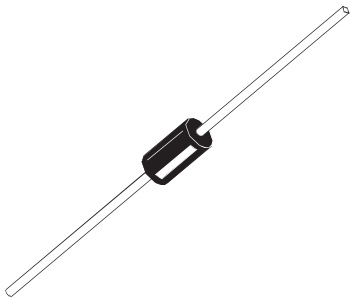
BAT47
BAT48

SMALL SIGNAL SCHOTTKY DIODE



DO-35

DESCRIPTION

General purpose, metal to silicon diodes featuring very low turn-on voltage and fast switching.These devices have integrated protection against excessive voltage such as electrostatic discharges.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		BAT47	BAT48	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		20	40	V
I_F	Forward Continuous Current*	T_a = 25°C	350		mA
I_{FRM}	Repetitive Peak Fordward Current*	$t_p \leq 1s$ $\delta \leq 0.5$	1		A
I_{FSM}	Surge non Repetitive Forward Current*	t_p = 10ms	7.5		A
		t_p = 1s	1.5		
P_{tot}	Power Dissipation*	T_a = 25°C	330		mW
T_{stg} T_j	Storage and Junction Temperature Range		- 65 to + 150 - 65 to + 125		°C °C
T_L	Maximum Temperature for Soldering during 10s at 4mm from Case		230		°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-l)}$	Junction-ambient*	300	°C/W

* On infinite heatsink with 4mm lead length

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
$V_{(BR)}$	I_R = 10µA		BAT47	20			V
	I_R = 25µA		BAT48	40			
V_F*	T_j = 25°C I_F = 0.1mA		All Types			0.25	V
	T_j = 25°C I_F = 1mA					0.3	
	T_j = 25°C I_F = 10mA					0.4	
	T_j = 25°C I_F = 30mA		BAT47			0.5	
	T_j = 25°C I_F = 150mA					0.8	
	T_j = 25°C I_F = 300mA					1	
	T_j = 25°C I_F = 50mA		BAT48			0.5	
	T_j = 25°C I_F = 200mA					0.75	
	T_j = 25°C I_F = 500mA					0.9	
I_R*	T_j = 25°C	V_R = 1.5V	All Types			1	µA
	T_j = 60°C					10	
	T_j = 25°C	V_R = 10V	BAT47			4	
	T_j = 60°C					20	
	T_j = 25°C	V_R = 20V				10	
	T_j = 60°C					30	
	T_j = 25°C	V_R = 10V	BAT48			2	
	T_j = 60°C					15	
	T_j = 25°C	V_R = 20V				5	
	T_j = 60°C					25	
	T_j = 25°C	V_R = 40V				25	
	T_j = 60°C					50	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C	T_j = 25°C V_R = 0V	f = 1MHz		20		pF
	T_j = 25°C V_R = 1V			12		

* Pulse test: $t_p \leq 300\mu s$ $\delta < 2\%$.

Fig. 1: Forward current versus forward voltage at different temperatures (typical values).

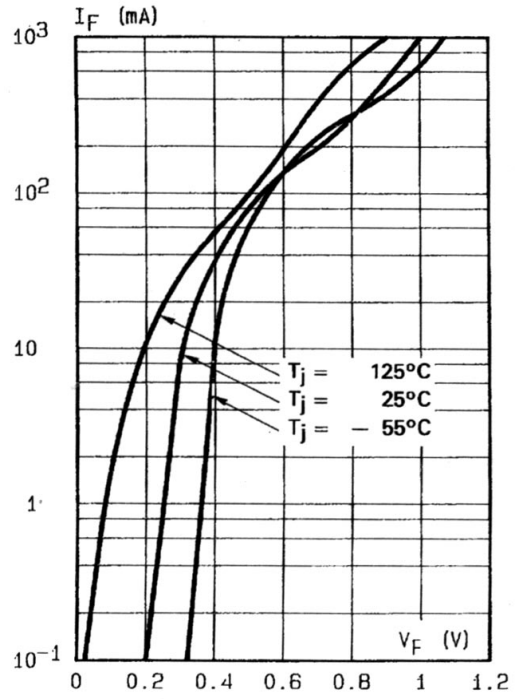


Fig. 2: Forward current versus forward voltage (typical values).

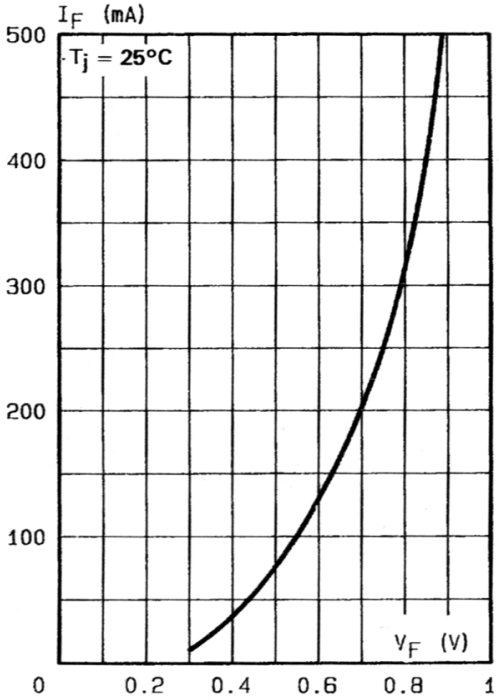


Fig. 3: Reverse current versus junction temperature.

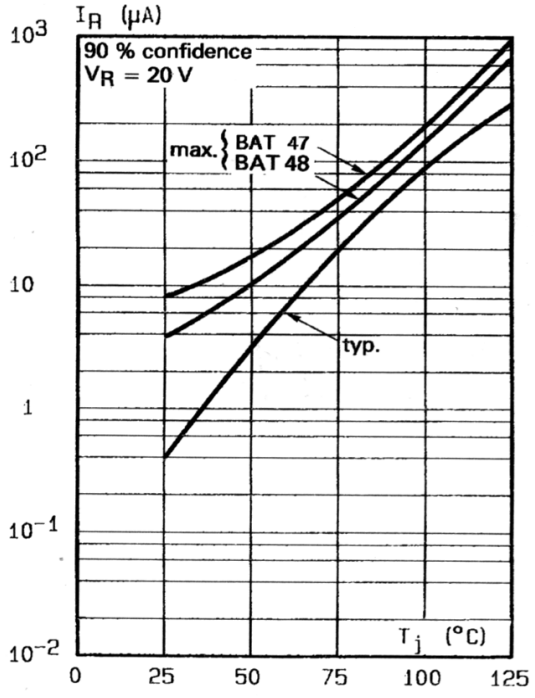


Fig. 4: Reverse current versus continuous reverse voltage (typical values).

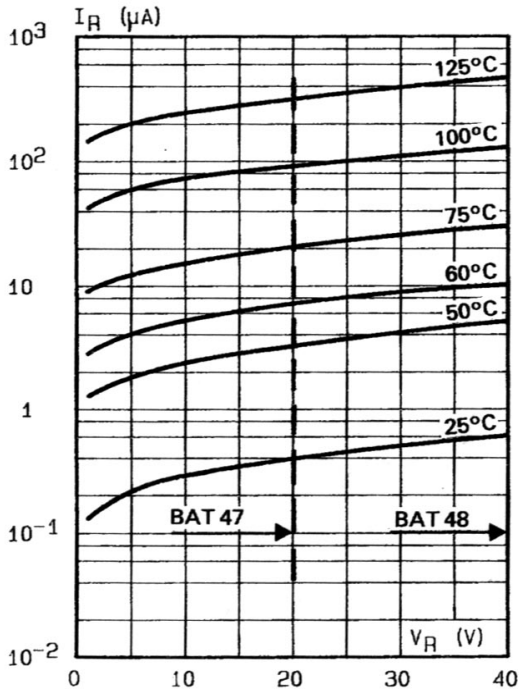
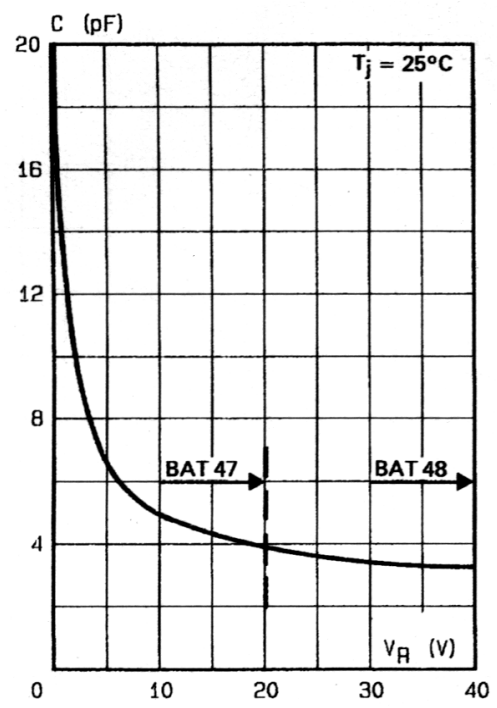
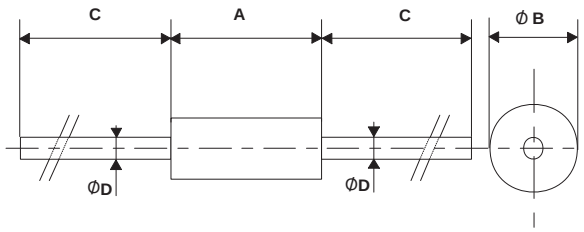


Fig. 5: Capacitance C versus reverse applied voltage V_R (typical values).



PACKAGE MECHANICAL DATA
DO-35



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	3.05	4.50	0.120	0.177
B	1.53	2.00	0.060	0.079
C	28.00		1.102	
D	0.458	0.558	0.018	0.022

Cooling method: by convection and conduction.
Marking: clear, ring at cathode end.
Weight: 0.015g

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